# E.J. Lattice Semiconductor Corporation - <u>LFXP2-30E-5FN672I Datasheet</u>



Welcome to E-XFL.COM

#### Understanding <u>Embedded - FPGAs (Field</u> <u>Programmable Gate Array)</u>

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

#### **Applications of Embedded - FPGAs**

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

#### Details

Product Status	Active
Number of LABs/CLBs	3625
Number of Logic Elements/Cells	29000
Total RAM Bits	396288
Number of I/O	472
Number of Gates	-
Voltage - Supply	1.14V ~ 1.26V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	672-BBGA
Supplier Device Package	672-FPBGA (27x27)
Purchase URL	https://www.e-xfl.com/product-detail/lattice-semiconductor/lfxp2-30e-5fn672i

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong



# LatticeXP2 Family Data Sheet Introduction

#### February 2012

### Features

- flexiFLASH<sup>™</sup> Architecture
  - Instant-on
  - Infinitely reconfigurable
  - Single chip
  - FlashBAK<sup>™</sup> technology
  - Serial TAG memory
  - Design security

#### Live Update Technology

- TransFR<sup>™</sup> technology
- Secure updates with 128 bit AES encryption
- Dual-boot with external SPI

#### ■ sysDSP<sup>™</sup> Block

- Three to eight blocks for high performance Multiply and Accumulate
- 12 to 32 18x18 multipliers
- Each block supports one 36x36 multiplier or four 18x18 or eight 9x9 multipliers

#### Embedded and Distributed Memory

- Up to 885 Kbits sysMEM<sup>™</sup> EBR
- Up to 83 Kbits Distributed RAM

#### ■ sysCLOCK<sup>™</sup> PLLs

- Up to four analog PLLs per device
- Clock multiply, divide and phase shifting

## Flexible I/O Buffer

- sysIO<sup>™</sup> buffer supports:
  - LVCMOS 33/25/18/15/12; LVTTL
  - SSTL 33/25/18 class I, II
  - HSTL15 class I; HSTL18 class I, II
  - PCI
  - LVDS, Bus-LVDS, MLVDS, LVPECL, RSDS
- Pre-engineered Source Synchronous Interfaces
  - DDR / DDR2 interfaces up to 200 MHz
  - 7:1 LVDS interfaces support display applications
  - XGMII
- Density And Package Options
  - 5k to 40k LUT4s, 86 to 540 I/Os
  - csBGA, TQFP, PQFP, ftBGA and fpBGA packages
  - Density migration supported
- Flexible Device Configuration
  - SPI (master and slave) Boot Flash Interface
  - Dual Boot Image supported
  - Soft Error Detect (SED) macro embedded

### System Level Support

- IEEE 1149.1 and IEEE 1532 Compliant
- · On-chip oscillator for initialization & general use
- Devices operate with 1.2V power supply

Device	XP2-5	XP2-8	XP2-17	XP2-30	XP2-40
LUTs (K)	5	8	17	29	40
Distributed RAM (KBits)	10	18	35	56	83
EBR SRAM (KBits)	166	221	276	387	885
EBR SRAM Blocks	9	12	15	21	48
sysDSP Blocks	3	4	5	7	8
18 x 18 Multipliers	12	16	20	28	32
V <sub>CC</sub> Voltage	1.2	1.2	1.2	1.2	1.2
GPLL	2	2	4	4	4
Max Available I/O	172	201	358	472	540
Packages and I/O Combinations					•
132-Ball csBGA (8 x 8 mm)	86	86			
144-Pin TQFP (20 x 20 mm)	100	100			
208-Pin PQFP (28 x 28 mm)	146	146	146		
256-Ball ftBGA (17 x17 mm)	172	201	201	201	
484-Ball fpBGA (23 x 23 mm)			358	363	363
672-Ball fpBGA (27 x 27 mm)				472	540

### Table 1-1. LatticeXP2 Family Selection Guide

#### Data Sheet DS1009

<sup>© 2012</sup> Lattice Semiconductor Corp. All Lattice trademarks, registered trademarks, patents, and disclaimers are as listed at www.latticesemi.com/legal. All other brand or product names are trademarks or registered trademarks of their respective holders. The specifications and information herein are subject to change without notice.



#### Figure 2-14. Slice0 through Slice2 Control Selection



### **Edge Clock Routing**

LatticeXP2 devices have eight high-speed edge clocks that are intended for use with the PIOs in the implementation of high-speed interfaces. Each device has two edge clocks per edge. Figure 2-15 shows the selection muxes for these clocks.

#### Figure 2-15. Edge Clock Mux Connections





## sysMEM Memory

LatticeXP2 devices contains a number of sysMEM Embedded Block RAM (EBR). The EBR consists of 18 Kbit RAM with dedicated input and output registers.

#### sysMEM Memory Block

The sysMEM block can implement single port, dual port or pseudo dual port memories. Each block can be used in a variety of depths and widths as shown in Table 2-5. FIFOs can be implemented in sysMEM EBR blocks by using support logic with PFUs. The EBR block supports an optional parity bit for each data byte to facilitate parity checking. EBR blocks provide byte-enable support for configurations with18-bit and 36-bit data widths.

#### Table 2-5. sysMEM Block Configurations

Memory Mode	Configurations
Single Port	16,384 x 1 8,192 x 2 4,096 x 4 2,048 x 9 1,024 x 18 512 x 36
True Dual Port	16,384 x 1 8,192 x 2 4,096 x 4 2,048 x 9 1,024 x 18
Pseudo Dual Port	16,384 x 1 8,192 x 2 4,096 x 4 2,048 x 9 1,024 x 18 512 x 36

### Bus Size Matching

All of the multi-port memory modes support different widths on each of the ports. The RAM bits are mapped LSB word 0 to MSB word 0, LSB word 1 to MSB word 1, and so on. Although the word size and number of words for each port varies, this mapping scheme applies to each port.

### FlashBAK EBR Content Storage

All the EBR memory in the LatticeXP2 is shadowed by Flash memory. Optionally, initialization values for the memory blocks can be defined using the Lattice Diamond design tools. The initialization values are loaded into the Flash memory during device programming and into the SRAM at power up or whenever the device is reconfigured. This feature is ideal for the storage of a variety of information such as look-up tables and microprocessor code. It is also possible to write the current contents of the EBR memory back to Flash memory. This capability is useful for the storage of data such as error codes and calibration information. For additional information on the FlashBAK capability see TN1137, LatticeXP2 Memory Usage Guide.



- In the 'Signed/Unsigned' options the operands can be switched between signed and unsigned on every cycle.
- In the 'Add/Sub' option the Accumulator can be switched between addition and subtraction on every cycle.
- The loading of operands can switch between parallel and serial operations.

### **MULT sysDSP Element**

This multiplier element implements a multiply with no addition or accumulator nodes. The two operands, A and B, are multiplied and the result is available at the output. The user can enable the input/output and pipeline registers. Figure 2-20 shows the MULT sysDSP element.

#### Figure 2-20. MULT sysDSP Element





register. Similarly, CE and RST are selected from their four respective sources (CE0, CE1, CE2, CE3 and RST0, RST1, RST2, RST3) at each input register, pipeline register and output register.

### Signed and Unsigned with Different Widths

The DSP block supports other widths, in addition to x9, x18 and x36 widths, of signed and unsigned multipliers. For unsigned operands, unused upper data bits should be filled to create a valid x9, x18 or x36 operand. For signed two's complement operands, sign extension of the most significant bit should be performed until x9, x18 or x36 width is reached. Table 2-7 provides an example of this.

#### Table 2-7. Sign Extension Example

Number	Unsigned	Unsigned 9-bit	Unsigned 18-bit	Signed	Two's Complement Signed 9 Bits	Two's Complement Signed 18 Bits
+5	0101	000000101	00000000000000101	0101	00000101	00000000000000101
-6	N/A	N/A	N/A	1010	111111010	1111111111111111010

### **OVERFLOW Flag from MAC**

The sysDSP block provides an overflow output to indicate that the accumulator has overflowed. "Roll-over" occurs and an overflow signal is indicated when any of the following is true: two unsigned numbers are added and the result is a smaller number than the accumulator, two positive numbers are added with a negative sum or two negative numbers are added with a positive sum. Note that when overflow occurs the overflow flag is present for only one cycle. By counting these overflow pulses in FPGA logic, larger accumulators can be constructed. The conditions for the overflow signal for signed and unsigned operands are listed in Figure 2-24.

#### Figure 2-24. Accumulator Overflow/Underflow





## Programmable I/O Cells (PIC)

Each PIC contains two PIOs connected to their respective sysIO buffers as shown in Figure 2-25. The PIO Block supplies the output data (DO) and the tri-state control signal (TO) to the sysIO buffer and receives input from the buffer. Table 2-11 provides the PIO signal list.

#### Figure 2-25. PIC Diagram



Signals are available on left/right/bottom edges only.
 Selected blocks.

Two adjacent PIOs can be joined to provide a differential I/O pair (labeled as "T" and "C") as shown in Figure 2-25. The PAD Labels "T" and "C" distinguish the two PIOs. Approximately 50% of the PIO pairs on the left and right edges of the device can be configured as true LVDS outputs. All I/O pairs can operate as inputs.



#### Table 2-11. PIO Signal List

Name	Туре	Description
CE	Control from the core	Clock enables for input and output block flip-flops
CLK	Control from the core	System clocks for input and output blocks
ECLK1, ECLK2	Control from the core	Fast edge clocks
LSR	Control from the core	Local Set/Reset
GSRN	Control from routing	Global Set/Reset (active low)
INCK <sup>2</sup>	Input to the core	Input to Primary Clock Network or PLL reference inputs
DQS	Input to PIO	DQS signal from logic (routing) to PIO
INDD	Input to the core	Unregistered data input to core
INFF	Input to the core	Registered input on positive edge of the clock (CLK0)
IPOS0, IPOS1	Input to the core	Double data rate registered inputs to the core
QPOS0 <sup>1</sup> , QPOS1 <sup>1</sup>	Input to the core	Gearbox pipelined inputs to the core
QNEG0 <sup>1</sup> , QNEG1 <sup>1</sup>	Input to the core	Gearbox pipelined inputs to the core
OPOS0, ONEG0, OPOS2, ONEG2	Output data from the core	Output signals from the core for SDR and DDR operation
OPOS1 ONEG1	Tristate control from the core	Signals to Tristate Register block for DDR operation
DEL[3:0]	Control from the core	Dynamic input delay control bits
TD	Tristate control from the core	Tristate signal from the core used in SDR operation
DDRCLKPOL	Control from clock polarity bus	Controls the polarity of the clock (CLK0) that feed the DDR input block
DQSXFER	Control from core	Controls signal to the Output block

1. Signals available on left/right/bottom only.

2. Selected I/O.

## PIO

The PIO contains four blocks: an input register block, output register block, tristate register block and a control logic block. These blocks contain registers for operating in a variety of modes along with necessary clock and selection logic.

### Input Register Block

The input register blocks for PIOs contain delay elements and registers that can be used to condition high-speed interface signals, such as DDR memory interfaces and source synchronous interfaces, before they are passed to the device core. Figure 2-26 shows the diagram of the input register block.

Input signals are fed from the sysIO buffer to the input register block (as signal DI). If desired, the input signal can bypass the register and delay elements and be used directly as a combinatorial signal (INDD), a clock (INCK) and, in selected blocks, the input to the DQS delay block. If an input delay is desired, designers can select either a fixed delay or a dynamic delay DEL[3:0]. The delay, if selected, reduces input register hold time requirements when using a global clock.

The input block allows three modes of operation. In the Single Data Rate (SDR) mode, the data is registered, by one of the registers in the SDR Sync register block, with the system clock. In DDR mode two registers are used to sample the data on the positive and negative edges of the DQS signal which creates two data streams, D0 and D2. D0 and D2 are synchronized with the system clock before entering the core. Further information on this topic can be found in the DDR Memory Support section of this data sheet.

By combining input blocks of the complementary PIOs and sharing registers from output blocks, a gearbox function can be implemented, that takes a double data rate signal applied to PIOA and converts it as four data streams, IPOS0A, IPOS1A, IPOS0B and IPOS1B. Figure 2-26 shows the diagram using this gearbox function. For more information on this topic, please see TN1138, LatticeXP2 High Speed I/O Interface.



shows the diagram using this gearbox function. For more information on this topic, see TN1138, <u>LatticeXP2 High</u> <u>Speed I/O Interface</u>.







#### Figure 2-31. DQS Local Bus



\*DQSXFERDEL shifts ECLK1 by 90% and is not associated with a particular PIO.

## **Polarity Control Logic**

In a typical DDR memory interface design, the phase relationship between the incoming delayed DQS strobe and the internal system clock (during the READ cycle) is unknown. The LatticeXP2 family contains dedicated circuits to transfer data between these domains. To prevent set-up and hold violations, at the domain transfer between DQS (delayed) and the system clock, a clock polarity selector is used. This changes the edge on which the data is registered in the synchronizing registers in the input register block and requires evaluation at the start of each READ cycle for the correct clock polarity.

Prior to the READ operation in DDR memories, DQS is in tristate (pulled by termination). The DDR memory device drives DQS low at the start of the preamble state. A dedicated circuit detects this transition. This signal is used to control the polarity of the clock to the synchronizing registers.



and loaded directly onto test nodes, or test data to be captured and shifted out for verification. The test access port consists of dedicated I/Os: TDI, TDO, TCK and TMS. The test access port has its own supply voltage  $V_{CCJ}$  and can operate with LVCMOS3.3, 2.5, 1.8, 1.5 and 1.2 standards. For more information, please see TN1141, LatticeXP2 sysCONFIG Usage Guide.

## flexiFLASH Device Configuration

The LatticeXP2 devices combine Flash and SRAM on a single chip to provide users with flexibility in device programming and configuration. Figure 2-33 provides an overview of the arrangement of Flash and SRAM configuration cells within the device. The remainder of this section provides an overview of these capabilities. See TN1141, LatticeXP2 sysCONFIG Usage Guide for a more detailed description.



Figure 2-33. Overview of Flash and SRAM Configuration Cells Within LatticeXP2 Devices

At power-up, or on user command, data is transferred from the on-chip Flash memory to the SRAM configuration cells that control the operation of the device. This is done with massively parallel buses enabling the parts to operate within microseconds of the power supplies reaching valid levels; this capability is referred to as Instant-On.

The on-chip Flash enables a single-chip solution eliminating the need for external boot memory. This Flash can be programmed through either the JTAG or Slave SPI ports of the device. The SRAM configuration space can also be infinitely reconfigured through the JTAG and Master SPI ports. The JTAG port is IEEE 1149.1 and IEEE 1532 compliant.

As described in the EBR section of the data sheet, the FlashBAK capability of the parts enables the contents of the EBR blocks to be written back into the Flash storage area without erasing or reprogramming other aspects of the device configuration. Serial TAG memory is also available to allow the storage of small amounts of data such as calibration coefficients and error codes.

For applications where security is important, the lack of an external bitstream provides a solution that is inherently more secure than SRAM only FPGAs. This is further enhanced by device locking. The device can be in one of three modes:



## Hot Socketing Specifications<sup>1, 2, 3, 4</sup>

Symbol	Parameter	Condition	Min.	Тур.	Max.	Units
I <sub>DK</sub>	Input or I/O Leakage Current	$0 \le V_{IN} \le V_{IH}$ (MAX.)	_	_	+/-1	mA

1. Insensitive to sequence of  $V_{CC}$ ,  $V_{CCAUX}$  and  $V_{CCIO}$ . However, assumes monotonic rise/fall rates for  $V_{CC}$ ,  $V_{CCAUX}$  and  $V_{CCIO}$ .

2.  $0 \le V_{CC} \le V_{CC}$  (MAX),  $0 \le V_{CCIO} \le V_{CCIO}$  (MAX) or  $0 \le V_{CCAUX} \le V_{CCAUX}$  (MAX).

3.  $I_{DK}$  is additive to  $I_{PU}$ ,  $I_{PW}$  or  $I_{BH}$ .

4. LVCMOS and LVTTL only.

## **ESD** Performance

Please refer to the <u>LatticeXP2 Product Family Qualification Summary</u> for complete qualification data, including ESD performance.

## **DC Electrical Characteristics**

Symbol	Parameter	Condition	Min.	Тур.	Max.	Units
I., I., <sup>1</sup>		$0 \le V_{IN} \le V_{CCIO}$	—		10	μΑ
ιL', ιΗ	input of i/O Low Leakage	$V_{CCIO} \le V_{IN} \le V_{IH}$ (MAX)	—	_	150	μΑ
I <sub>PU</sub>	I/O Active Pull-up Current	$0 \le V_{IN} \le 0.7 \ V_{CCIO}$	-30	—	-150	μΑ
I <sub>PD</sub>	I/O Active Pull-down Current	$V_{IL}$ (MAX) $\leq V_{IN} \leq V_{CCIO}$	30		210	μΑ
I <sub>BHLS</sub>	Bus Hold Low Sustaining Current	$V_{IN} = V_{IL}$ (MAX)	30	—	—	μΑ
I <sub>BHHS</sub>	Bus Hold High Sustaining Current	$V_{IN} = 0.7 V_{CCIO}$	-30	—	—	μΑ
I <sub>BHLO</sub>	Bus Hold Low Overdrive Current	$0 \le V_{IN} \le V_{CCIO}$	—		210	μΑ
I <sub>BHHO</sub>	Bus Hold High Overdrive Current	$0 \le V_{IN} \le V_{CCIO}$	—	—	-150	μΑ
V <sub>BHT</sub>	Bus Hold Trip Points		$V_{IL}$ (MAX)	_	V <sub>IH</sub> (MIN)	V
C1	I/O Capacitance <sup>2</sup>	$V_{CCIO} = 3.3V, 2.5V, 1.8V, 1.5V, 1.2V, V_{CC} = 1.2V, V_{IO} = 0 \text{ to } V_{IH} \text{ (MAX)}$	—	8	—	pf
C2	Dedicated Input Capacitance	$V_{CCIO} = 3.3V, 2.5V, 1.8V, 1.5V, 1.2V, V_{CC} = 1.2V, V_{IO} = 0 \text{ to } V_{IH} \text{ (MAX)}$	—	6	—	pf

#### **Over Recommended Operating Conditions**

1. Input or I/O leakage current is measured with the pin configured as an input or as an I/O with the output driver tri-stated. It is not measured with the output driver active. Bus maintenance circuits are disabled.

2. T<sub>A</sub> 25°C, f = 1.0 MHz.



## Supply Current (Standby)<sup>1, 2, 3, 4</sup>

Symbol	Parameter	Device	Typical⁵	Units
		XP2-5	14	mA
		XP2-8	18	mA
I <sub>CC</sub>	Core Power Supply Current	XP2-17	24	mA
		XP2-30	35	mA
		XP2-40	45	mA
		XP2-5	15	mA
		XP2-8	15	mA
I <sub>CCAUX</sub>	Auxiliary Power Supply Current <sup>6</sup>	XP2-17	15	mA
		XP2-30	16	mA
		XP2-40	16	mA
I <sub>CCPLL</sub>	PLL Power Supply Current (per PLL)		0.1	mA
I <sub>CCIO</sub>	Bank Power Supply Current (per bank)		2	mA
ICCJ	V <sub>CCJ</sub> Power Supply Current		0.25	mA

#### **Over Recommended Operating Conditions**

1. For further information on supply current, please see TN1139, Power Estimation and Management for LatticeXP2 Devices.

2. Assumes all outputs are tristated, all inputs are configured as LVCMOS and held at the V<sub>CCIO</sub> or GND.

3. Frequency 0 MHz.

4. Pattern represents a "blank" configuration data file.

5.  $T_J = 25^{\circ}C$ , power supplies at nominal voltage.

6. In fpBGA and ftBGA packages the PLLs are connected to and powered from the auxiliary power supply. For these packages, the actual auxiliary supply current is the sum of I<sub>CCAUX</sub> and I<sub>CCPLL</sub>. For csBGA, PQFP and TQFP packages the PLLs are powered independent of the auxiliary power supply.



## sysIO Recommended Operating Conditions

		V <sub>CCIO</sub>		V <sub>REF</sub> (V)			
Standard	Min.	Тур.	Max.	Min.	Тур.	Max.	
LVCMOS33 <sup>2</sup>	3.135	3.3	3.465	—			
LVCMOS25 <sup>2</sup>	2.375	2.5	2.625	—			
LVCMOS18	1.71	1.8	1.89	—	—	—	
LVCMOS15	1.425	1.5	1.575	—			
LVCMOS12 <sup>2</sup>	1.14	1.2	1.26	—			
LVTTL33 <sup>2</sup>	3.135	3.3	3.465	—	—	—	
PCI33	3.135	3.3	3.465	—		—	
SSTL18_I <sup>2</sup> , SSTL18_II <sup>2</sup>	1.71	1.8	1.89	0.833	0.9	0.969	
SSTL25_I <sup>2</sup> , SSTL25_II <sup>2</sup>	2.375	2.5	2.625	1.15	1.25	1.35	
SSTL33_I <sup>2</sup> , SSTL33_II <sup>2</sup>	3.135	3.3	3.465	1.3	1.5	1.7	
HSTL15_l <sup>2</sup>	1.425	1.5	1.575	0.68	0.75	0.9	
HSTL18_I <sup>2</sup> , HSTL18_II <sup>2</sup>	1.71	1.8	1.89	0.816	0.9	1.08	
LVDS25 <sup>2</sup>	2.375	2.5	2.625	—			
MLVDS251	2.375	2.5	2.625	—			
LVPECL33 <sup>1, 2</sup>	3.135	3.3	3.465	—			
BLVDS25 <sup>1, 2</sup>	2.375	2.5	2.625	—			
RSDS <sup>1, 2</sup>	2.375	2.5	2.625	—			
SSTL18D_I <sup>2</sup> , SSTL18D_II <sup>2</sup>	1.71	1.8	1.89	—	—	—	
SSTL25D_ I <sup>2</sup> , SSTL25D_II <sup>2</sup>	2.375	2.5	2.625	—	—	—	
SSTL33D_ I <sup>2</sup> , SSTL33D_ II <sup>2</sup>	3.135	3.3	3.465	—	—	—	
HSTL15D_ I <sup>2</sup>	1.425	1.5	1.575	—	—	—	
HSTL18D_ I <sup>2</sup> , HSTL18D_ II <sup>2</sup>	1.71	1.8	1.89	_	—	—	

#### **Over Recommended Operating Conditions**

1. Inputs on chip. Outputs are implemented with the addition of external resistors. 2. Input on this standard does not depend on the value of  $V_{CCIO}$ .



## sysIO Single-Ended DC Electrical Characteristics

Input/Output	Input/Output V <sub>IL</sub>		V <sub>IH</sub>		V <sub>OL</sub>	V <sub>OH</sub>			
Standard	Min. (V)	Max. (V)	Min. (V)	Max. (V)	Max. (V)	Min. (V)	l <sub>OL</sub> 1 (mA)	l <sub>OH</sub> ¹ (mA)	
LVCMOS33	-0.3	0.8	2.0	3.6	0.4	V <sub>CCIO</sub> - 0.4	20, 16, 12, 8, 4	-20, -16, -12, -8, -4	
					0.2	V <sub>CCIO</sub> - 0.2	0.1	-0.1	
LVTTL33	-0.3	0.8	2.0	3.6	0.4	V <sub>CCIO</sub> - 0.4	20, 16, 12, 8, 4	-20, -16, -12, -8, -4	
					0.2	V <sub>CCIO</sub> - 0.2	0.1	-0.1	
LVCMOS25	-0.3	0.7	1.7	3.6	0.4	V <sub>CCIO</sub> - 0.4	20, 16, 12, 8, 4	-20, -16, -12, -8, -4	
					0.2	V <sub>CCIO</sub> - 0.2	0.1	-0.1	
LVCMOS18	-0.3	0.35 V <sub>CCIO</sub>	0.65 V <sub>CCIO</sub>	3.6	0.4	V <sub>CCIO</sub> - 0.4	16, 12, 8, 4	-16, -12, -8, -4	
					0.2	V <sub>CCIO</sub> - 0.2	0.1	-0.1	
	0.2	0.25 \/	0.65 \	2.6	0.4	V <sub>CCIO</sub> - 0.4	8, 4	-8, -4	
	-0.3	0.35 VCCIO	0.05 V CCIO	5.0	0.2	V <sub>CCIO</sub> - 0.2	0.1	-0.1	
	-0.3	0.35 V	0.65 V	3.6	0.4	V <sub>CCIO</sub> - 0.4	6, 2	-6, -2	
	-0.5	0.35 V <sub>CC</sub>	0.05 V <sub>CC</sub>	0.0	0.2	V <sub>CCIO</sub> - 0.2	0.1	-0.1	
PCI33	-0.3	0.3 V <sub>CCIO</sub>	0.5 V <sub>CCIO</sub>	3.6	0.1 V <sub>CCIO</sub>	0.9 V <sub>CCIO</sub>	1.5	-0.5	
SSTL33_I	-0.3	V <sub>REF</sub> - 0.2	V <sub>REF</sub> + 0.2	3.6	0.7	V <sub>CCIO</sub> - 1.1	8	-8	
SSTL33_II	-0.3	V <sub>REF</sub> - 0.2	V <sub>REF</sub> + 0.2	3.6	0.5	V <sub>CCIO</sub> - 0.9	16	-16	
SSTI 25 I	-0.3	-0.3 V	Vpcc - 0 18	V 0 18	3.6	0.54	Vacua - 0.62	7.6	-7.6
001220_1	-0.0	VREF - 0.10	VREF + 0.10	0.0	0.04	ACCIO - 0.05	12	-12	
SSTI 25 II	-0.3	V0 18	V+0 18	36	0.35	Vac: a 0.43	15.2	-15.2	
001225_11	-0.0	VREF - 0.10	VREF + 0.10	0.0	0.00	V <sub>CCIO</sub> - 0.43	20	-20	
SSTL18_I	-0.3	V <sub>REF</sub> - 0.125	V <sub>REF</sub> + 0.125	3.6	0.4	V <sub>CCIO</sub> - 0.4	6.7	-6.7	
	-0.3	V 0 125	V+0 125	36	0.28	Vac 0.28	8	-8	
001210_1	-0.0	VREF - 0.120	VREF + 0.120	0.0	0.20	VCCIO - 0.20	11	-11	
HSTI 15 I	-0.3	Vpcc - 0 1		3.6	0.4		4	-4	
	0.0	VREF 0.1	v <sub>REF</sub> + 0.1	0.0	0.4	VCCID 0.4	8	-8	
HSTI 18 I	-0.3	Vp== - 0 1		3.6	0.4		8	-8	
	0.0	KEF - 0.1		0.0	U.7		12	-12	
HSTL18_II	-0.3	V <sub>REF</sub> - 0.1	V <sub>REF</sub> + 0.1	3.6	0.4	V <sub>CCIO</sub> - 0.4	16	-16	

#### **Over Recommended Operating Conditions**

 The average DC current drawn by I/Os between GND connections, or between the last GND in an I/O bank and the end of an I/O bank, as shown in the logic signal connections table shall not exceed n \* 8mA, where n is the number of I/Os between bank GND connections or between the last GND in a bank and the end of a bank.



## **Register-to-Register Performance (Continued)**

Function	-7 Timing	Units
DSP IP Functions		
16-Tap Fully-Parallel FIR Filter	198	MHz
1024-pt FFT	221	MHz
8X8 Matrix Multiplication	196	MHz

1. These timing numbers were generated using the ispLEVER design tool. Exact performance may vary with device, design and tool version. The tool uses internal parameters that have been characterized but are not tested on every device.

## **Derating Timing Tables**

Logic timing provided in the following sections of this data sheet and the Diamond design tools are worst case numbers in the operating range. Actual delays at nominal temperature and voltage for best case process, can be much better than the values given in the tables. The Diamond design tool can provide logic timing numbers at a particular temperature and voltage.



## LatticeXP2 Internal Switching Characteristics<sup>1</sup>

		-7		-6		-5		
Parameter	Description	Min.	Max.	Min.	Max.	Min.	Max.	Units
PFU/PFF Logi	c Mode Timing				I			I
t <sub>LUT4_PFU</sub>	LUT4 delay (A to D inputs to F output)	_	0.216	_	0.238	_	0.260	ns
t <sub>LUT6_PFU</sub>	LUT6 delay (A to D inputs to OFX output)	—	0.304		0.399		0.494	ns
t <sub>LSR_PFU</sub>	Set/Reset to output of PFU (Asyn- chronous)	—	0.720		0.769		0.818	ns
t <sub>SUM_PFU</sub>	Clock to Mux (M0,M1) Input Setup Time	0.154	_	0.151	—	0.148	_	ns
t <sub>HM_PFU</sub>	Clock to Mux (M0,M1) Input Hold Time	-0.061	—	-0.057	—	-0.053	—	ns
t <sub>SUD_PFU</sub>	Clock to D input setup time	0.061	—	0.077	—	0.093	—	ns
t <sub>HD_PFU</sub>	Clock to D input hold time	0.002	—	0.003	—	0.003	—	ns
t <sub>CK2Q_PFU</sub>	Clock to Q delay, (D-type Register Configuration)	—	0.342	—	0.363	—	0.383	ns
t <sub>RSTREC_PFU</sub>	Asynchronous reset recovery time for PFU Logic	—	0.520		0.634		0.748	ns
t <sub>RST_PFU</sub>	Asynchronous reset time for PFU Logic	_	0.720	—	0.769	—	0.818	ns
PFU Dual Por	t Memory Mode Timing							
t <sub>CORAM_PFU</sub>	Clock to Output (F Port)	—	1.082	—	1.267	—	1.452	ns
t <sub>SUDATA_PFU</sub>	Data Setup Time	-0.206	—	-0.240	_	-0.274	—	ns
t <sub>HDATA_PFU</sub>	Data Hold Time	0.239	—	0.275	_	0.312	—	ns
t <sub>SUADDR_PFU</sub>	Address Setup Time	-0.294	—	-0.333	_	-0.371	—	ns
t <sub>HADDR_PFU</sub>	Address Hold Time	0.295	—	0.333	_	0.371	—	ns
t <sub>SUWREN_PFU</sub>	Write/Read Enable Setup Time	-0.146	—	-0.169	_	-0.193	—	ns
t <sub>HWREN_PFU</sub>	Write/Read Enable Hold Time	0.158	—	0.182	_	0.207	—	ns
PIO Input/Out	put Buffer Timing							
t <sub>IN_PIO</sub>	Input Buffer Delay (LVCMOS25)	_	0.858	—	0.766	—	0.674	ns
t <sub>OUT_PIO</sub>	Output Buffer Delay (LVCMOS25)	_	1.561	—	1.403	—	1.246	ns
IOLOGIC Inpu	t/Output Timing							
t <sub>SUI_PIO</sub>	Input Register Setup Time (Data Before Clock)	0.583	_	0.893	_	1.201	_	ns
t <sub>HI_PIO</sub>	Input Register Hold Time (Data after Clock)	0.062	_	0.322	_	0.482	_	ns
t <sub>COO_PIO</sub>	Output Register Clock to Output Delay	_	0.608	_	0.661	_	0.715	ns
t <sub>SUCE_PIO</sub>	Input Register Clock Enable Setup Time	0.032	_	0.037	_	0.041	_	ns
t <sub>HCE_PIO</sub>	Input Register Clock Enable Hold Time	-0.022	_	-0.025	—	-0.028	_	ns
t <sub>SULSR_PIO</sub>	Set/Reset Setup Time	0.184	—	0.201	—	0.217	—	ns
t <sub>HLSR_PIO</sub>	Set/Reset Hold Time	-0.080	—	-0.086	—	-0.093	—	ns
t <sub>RSTREC_PIO</sub>	Asynchronous reset recovery time for IO Logic	0.228	_	0.247	_	0.266	_	ns

### **Over Recommended Operating Conditions**



## LatticeXP2 Internal Switching Characteristics<sup>1</sup> (Continued)

		-7		-6		-5		
Parameter	Description	Min.	Max.	Min.	Max.	Min.	Max.	Units
t <sub>HP_DSP</sub>	Pipeline Register Hold Time	-0.787	_	-0.890	_	-0.994	—	ns
t <sub>SUO_DSP</sub>	Output Register Setup Time	4.896	—	5.413	—	5.931	—	ns
t <sub>HO_DSP</sub>	Output Register Hold Time	-1.439	—	-1.604	—	-1.770	—	ns
t <sub>COI_DSP</sub> <sup>3</sup>	Input Register Clock to Output Time	_	4.513	_	4.947	—	5.382	ns
t <sub>COP_DSP</sub> <sup>3</sup>	Pipeline Register Clock to Output Time	_	2.153	_	2.272	—	2.391	ns
t <sub>COO_DSP</sub> <sup>3</sup>	Output Register Clock to Output Time	_	0.569	_	0.600	—	0.631	ns
t <sub>SUADSUB</sub>	AdSub Input Register Setup Time	-0.270	—	-0.298	_	-0.327	—	ns
t <sub>HADSUB</sub>	AdSub Input Register Hold Time	0.306	—	0.338	—	0.371	—	ns

### **Over Recommended Operating Conditions**

1. Internal parameters are characterized, but not tested on every device.

2. RST resets VCO and all counters in PLL.

3. These parameters include the Adder Subtractor block in the path.



# LatticeXP2 Family Timing Adders<sup>1, 2, 3, 4</sup> (Continued)

#### **Over Recommended Operating Conditions**

Buffer Type	Description	-7	-6	-5	Units
LVCMOS25_4mA	LVCMOS 2.5 4mA drive, slow slew rate	1.05	1.43	1.81	ns
LVCMOS25_8mA	LVCMOS 2.5 8mA drive, slow slew rate	0.78	1.15	1.52	ns
LVCMOS25_12mA	LVCMOS 2.5 12mA drive, slow slew rate	0.59	0.96	1.33	ns
LVCMOS25_16mA	LVCMOS 2.5 16mA drive, slow slew rate	0.81	1.18	1.55	ns
LVCMOS25_20mA	LVCMOS 2.5 20mA drive, slow slew rate	0.61	0.98	1.35	ns
LVCMOS18_4mA	LVCMOS 1.8 4mA drive, slow slew rate	1.01	1.38	1.75	ns
LVCMOS18_8mA	LVCMOS 1.8 8mA drive, slow slew rate	0.72	1.08	1.45	ns
LVCMOS18_12mA	LVCMOS 1.8 12mA drive, slow slew rate	0.53	0.90	1.26	ns
LVCMOS18_16mA	LVCMOS 1.8 16mA drive, slow slew rate	0.74	1.11	1.48	ns
LVCMOS15_4mA	LVCMOS 1.5 4mA drive, slow slew rate	0.96	1.33	1.71	ns
LVCMOS15_8mA	LVCMOS 1.5 8mA drive, slow slew rate	-0.53	-0.26	0.00	ns
LVCMOS12_2mA	LVCMOS 1.2 2mA drive, slow slew rate	0.90	1.27	1.65	ns
LVCMOS12_6mA	LVCMOS 1.2 6mA drive, slow slew rate	-0.55	-0.29	-0.02	ns
PCI33	3.3V PCI	-0.29	-0.01	0.26	ns

1. Timing Adders are characterized but not tested on every device.

2. LVCMOS timing measured with the load specified in Switching Test Condition table.

3. All other standards tested according to the appropriate specifications.

4. The base parameters used with these timing adders to calculate timing are listed in the LatticeXP2 Internal Switching Characteristics table under PIO Input/Output Timing.

5. These timing adders are measured with the recommended resistor values.



# LatticeXP2 Family Data Sheet Pinout Information

#### February 2012

Data Sheet DS1009

Signal Descriptions						
Signal Name	I/O	Description				
General Purpose		l				
	1/0	[Edge] indicates the edge of the device on which the pad is located. Valid edge designations are L (Left), B (Bottom), R (Right), T (Top).				
P[Edae] [Row/Column Number*] [A/B]		[Row/Column Number] indicates the PFU row or the column of the device on which the PIC exists. When Edge is T (Top) or B (Bottom), only need to specify Row Number. When Edge is L (Left) or R (Right), only need to specify Column Number.				
		[A/B] indicates the PIO within the PIC to which the pad is connected. Some of these user-programmable pins are shared with special function pins. These pins, when not used as special purpose pins, can be programmed as I/Os for user logic. During configuration the user-programmable I/Os are tri-stated with an internal pull-up resistor enabled. If any pin is not used (or not bonded to a package pin), it is also tri-stated with an internal pull-up resistor enabled after configuration.				
GSRN	I	Global RESET signal (active low). Any I/O pin can be GSRN.				
NC	—	No connect.				
GND		Ground. Dedicated pins.				
V <sub>CC</sub>		Power supply pins for core logic. Dedicated pins.				
V <sub>CCAUX</sub> —		Auxiliary power supply pin. This dedicated pin powers all the differential and referenced input buffers.				
V <sub>CCPLL</sub>		PLL supply pins. csBGA, PQFP and TQFP packages only.				
V <sub>CCIOx</sub>		Dedicated power supply pins for I/O bank x.				
V <sub>REF1_x</sub> , V <sub>REF2_x</sub>	_	Reference supply pins for I/O bank x. Pre-determined pins in each bank are assigned as $V_{\text{REF}}$ inputs. When not used, they may be used as I/O pins.				
PLL and Clock Functions (Used as us	er prog	ammable I/O pins when not in use for PLL or clock pins)				
[LOC][num]_V <sub>CCPLL</sub>		Power supply pin for PLL: LLC, LRC, URC, ULC, num = row from center.				
[LOC][num]_GPLL[T, C]_IN_A	I	General Purpose PLL (GPLL) input pads: LLC, LRC, URC, ULC, num = row from center, $T = true$ and $C = complement$ , index A,B,Cat each side.				
[LOC][num]_GPLL[T, C]_FB_A	I	Optional feedback GPLL input pads: LLC, LRC, URC, ULC, num = row from center, $T =$ true and $C =$ complement, index A,B,Cat each side.				
PCLK[T, C]_[n:0]_[3:0]		Primary Clock pads, $T =$ true and $C =$ complement, n per side, indexed by bank and 0,1,2,3 within bank.				
[LOC]DQS[num]	I	DQS input pads: T (Top), R (Right), B (Bottom), L (Left), DQS, num = ball function number. Any pad can be configured to be output.				
Test and Programming (Dedicated Pi	ns)					
TMS	I	Test Mode Select input, used to control the 1149.1 state machine. Pull-up is enabled during configuration.				
тск	I	Test Clock input pin, used to clock the 1149.1 state machine. No pull-up enabled.				
TDI I		Test Data in pin. Used to load data into device using 1149.1 state machine. After power-up, this TAP port can be activated for configuration by sending appropriate command. (Note: once a configuration port is selected it is locked. Another configuration port cannot be selected until the power-up				

# © 2012 Lattice Semiconductor Corp. All Lattice trademarks, registered trademarks, patents, and disclaimers are as listed at www.latticesemi.com/legal. All other brand or product names are trademarks or registered trademarks of their respective holders. The specifications and information herein are subject to change without notice.

sequence). Pull-up is enabled during configuration.



# LatticeXP2 Family Data Sheet Ordering Information

#### February 2012

Data Sheet DS1009

## **Part Number Description**



## **Ordering Information**

The LatticeXP2 devices are marked with a single temperature grade, either Commercial or Industrial, as shown below.



© 2012 Lattice Semiconductor Corp. All Lattice trademarks, registered trademarks, patents, and disclaimers are as listed at www.latticesemi.com/legal. All other brand or product names are trademarks or registered trademarks of their respective holders. The specifications and information herein are subject to change without notice.